
HM6207H Series

256 k High Speed SRAM (256-kword × 1-bit)

HITACHI

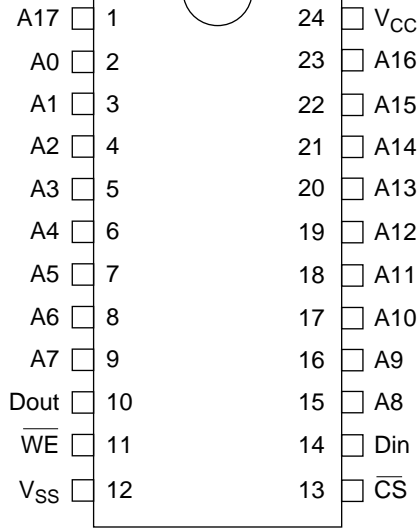
Features

- Single 5 V supply and high density 24-pin package
- High speed
Access time: 25/35/45 ns (max)
- Low power
 - Operation: 300 mW (typ)
 - Standby: 100 μ W (typ)
30 μ W (typ) (L-version)
- Completely static memory required, no clock or timing strobe required
- Equal access and cycle time
- Directly TTL compatible, all inputs and outputs
- Battery backup operation capability (L-version)

Ordering Information

Type No.	Access Time	Package
HM6207HP-25	25 ns	300-mil 24-pin plastic DIP (DP-24NC)
HM6207HP-35	35 ns	
HM6207HP-45	45 ns	
HM6207HLP-25	25 ns	300-mil 24-pin SOJ (CP-24D)
HM6207HLP-35	35 ns	
HM6207HLP-45	45 ns	
HM6207HJP-25	25 ns	300-mil 24-pin SOJ (CP-24D)
HM6207HJP-35	35 ns	
HM6207HJP-45	45 ns	
HM6207HLJP-25	25 ns	300-mil 24-pin SOJ (CP-24D)
HM6207HLJP-35	35 ns	
HM6207HLJP-45	45 ns	

Pin Arrangement

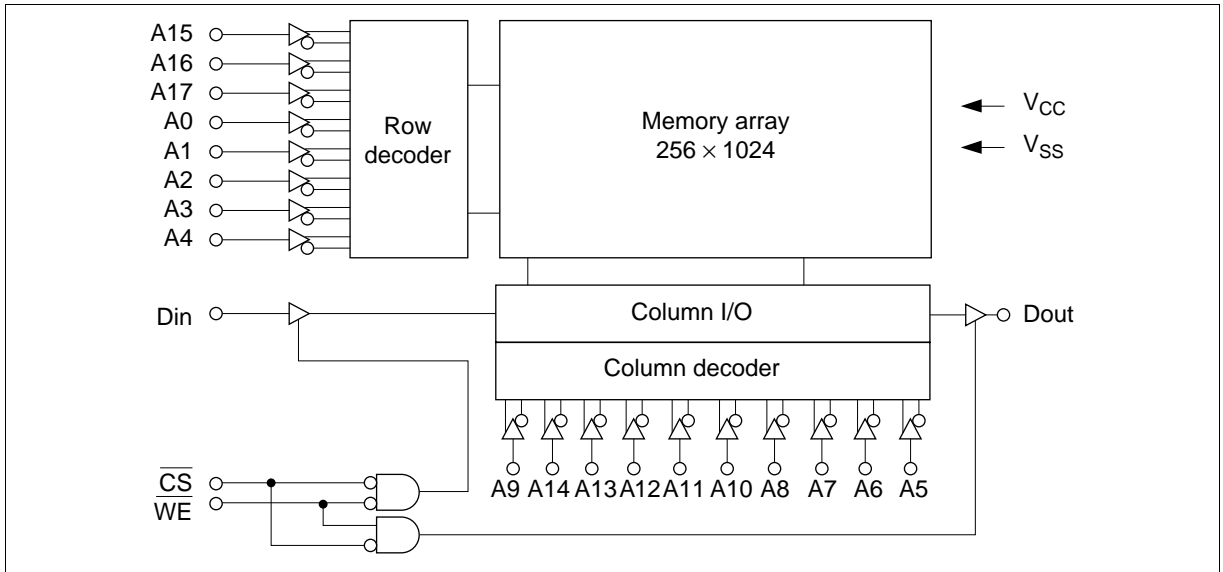


(Top view)

Pin Description

Pin Name	Function
A0–A17	Address
Din	Data input
Dout	Data output
\overline{CS}	Chip select
\overline{WE}	Write enable
V_{CC}	Power supply
V_{SS}	Ground

Block Diagram



Function Table

\overline{CS}	\overline{WE}	Mode	V_{CC} Current	I/O Pin	Ref. Cycle
H	×	Not selected	I_{SB}, I_{SB1}	High-Z	—
L	H	Read	I_{CC}	Dout	Read cycle
L	L	Write	I_{CC}	High-Z	Write cycle

Note: × = Don't care.

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	V_{in}	-0.5 ¹ to +7.0	V
Power dissipation	P_T	1.0	W
Operating temperature range	T_{opr}	0 to +70	°C
Storage temperature range	T_{stg}	-55 to +125	°C
Storage temperature range under bias	T_{bias}	-10 to +85	°C

Note: 1. $V_{in\ min} = -2.5\ V$ for pulse width < 10 ns.

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Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input high (logic 1) voltage	V_{IH}	2.2	—	6.0	V
Input low (logic 0) voltage	V_{IL}	-0.5 [†]	—	0.8	V

Note: 1. V_{IL} min = -2.0 V for pulse width \leq 10 ns.

DC Characteristics (Ta = 0 to +70°C, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	HM6207H-25		HM6207H-35/45		Unit	Test Conditions		
		Min	Typ [†]	Min	Typ [†]				
Input leakage current	I_{LI}	—	—	2.0	—	μA	$V_{CC} = \text{Max}$, $V_{in} = V_{SS}$ to V_{CC}		
Output leakage current	I_{LO}	—	—	10.0	—	μA	$\overline{CS} = V_{IH}$, $V_{I/O} = V_{SS}$ to V_{CC}		
Operating power supply current	I_{CC}	—	60	120	—	50	100	mA	$\overline{CS} = V_{IL}$, $I_{I/O} = 0\text{ mA}$, min cycle, duty = 100%
	I_{CC1}	—	40	80	—	40	80	mA	$\overline{CS} = V_{IL}$, $I_{I/O} = 0\text{ mA}$, t cycle = 50 ns, duty = 100%
Standby power supply current	I_{SB}	—	20	40	—	15	30	mA	$\overline{CS} = V_{IH}$, min cycle
Standby power supply current (1)	I_{SB1}	—	0.02	2.0	—	0.02	2.0	mA	$\overline{CS} \geq V_{CC} - 0.2\text{ V}$, $0\text{ V} \leq V_{in} < 0.2$, or $V_{in} \geq V_{CC} - 0.2\text{ V}$
	L- Version	—	0.006	0.1	—	0.006	0.1		
Output low voltage	V_{OL}	—	—	0.4	—	—	0.4	V	$I_{OL} = 8\text{ mA}$
Output high voltage	V_{OH}	2.4	—	—	2.4	—	—	V	$I_{OH} = -4.0\text{ mA}$

Note: 1. Typical values are at $V_{CC} = 5.0\text{ V}$, $T_a = +25^\circ\text{C}$ and not guaranteed.

Capacitance (Ta = 25°C, f = 1 MHz)^{*1}

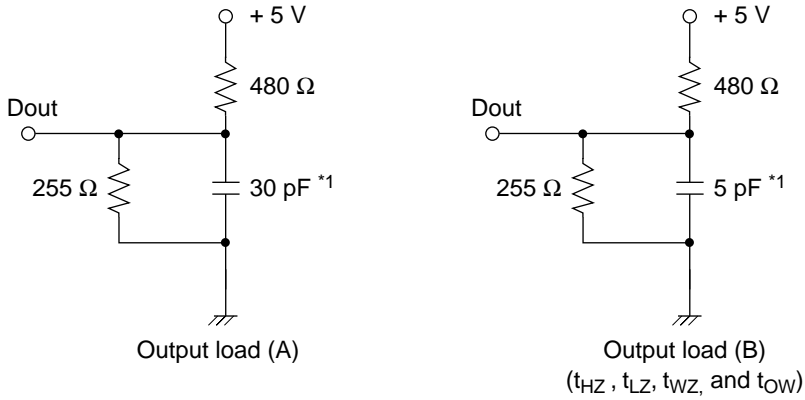
Parameter	Symbol	Min	Max	Unit	Test Conditions
Input capacitance	C_{in}	—	6	pF	$V_{in} = 0\text{ V}$
Output capacitance	C_{out}	—	10	pF	$V_{out} = 0\text{ V}$

Note: 1. This parameter is sampled and is not 100% tested.

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$ unless otherwise noted)

Test Conditions

- Input pulse levels: V_{SS} to 3.0 V
- Input and output timing reference levels: 1.5 V
- Input rise and fall time: 5 ns
- Output load: See figures



Note: 1. Including scope and jig

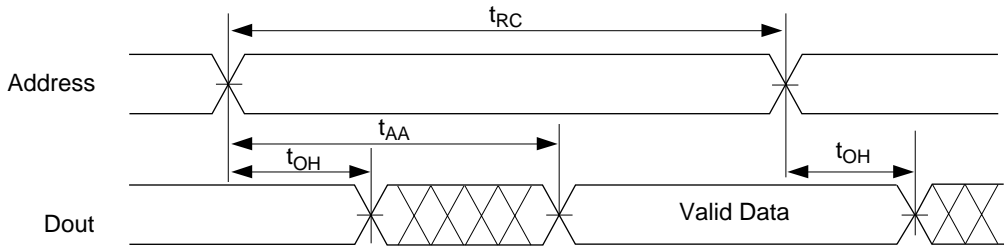
Read Cycle

Parameter	Symbol	HM6207H-25		HM6207H-35		HM6207H-45		Unit
		Min	Max	Min	Max	Min	Max	
Read cycle time	t_{RC}	25	—	35	—	45	—	ns
Address access time	t_{AA}	—	25	—	35	—	45	ns
Chip select access time	t_{ACS}	—	25	—	35	—	45	ns
Output hold from address change	t_{OH}	5	—	5	—	5	—	ns
Chip selection to output in low-Z	t_{LZ}^{-1}	5	—	5	—	5	—	ns
Chip deselection to output in high-Z	t_{HZ}^{-1}	0	15	0	20	0	20	ns

Note: 1. Transition is measured ± 200 mV from steady-state voltage with Load (B).

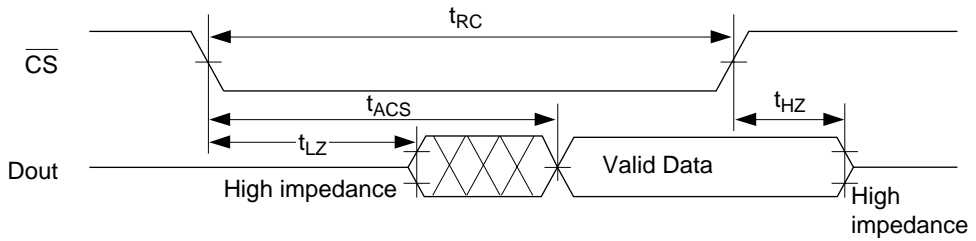
These parameters are sampled and not 100% tested.

Read Timing Waveform (1)



- Notes: 1. \overline{WE} is high for read cycle.
2. Device is continuously selected, $\overline{CS} = V_{IL}$.

Read Timing Waveform (2)



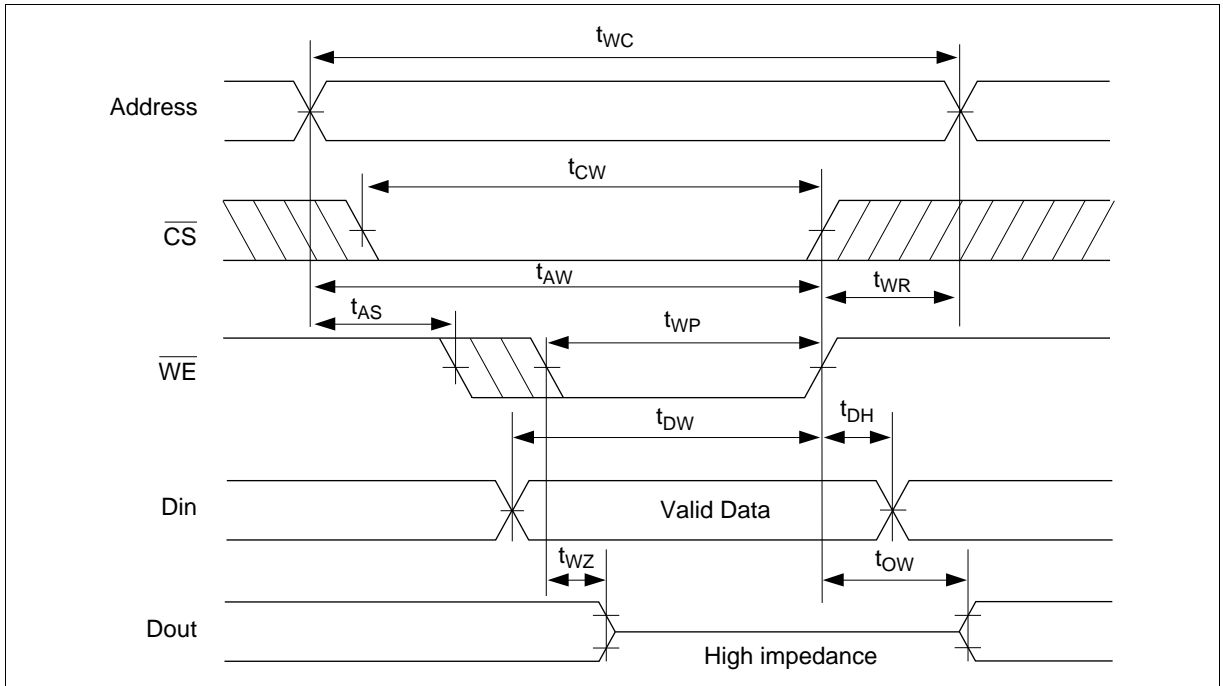
- Notes: 1. \overline{WE} is high for read cycle.
2. Address valid prior to coincident with \overline{CS} transition low.

Write Cycle

Parameter	Symbol	HM6207H-25		HM6207H-35		HM6207H-45		Unit
		Min	Max	Min	Max	Min	Max	
Write cycle time	t_{WC}	25	—	35	—	45	—	ns
Chip selection to end of write	t_{CW}	20	—	30	—	40	—	ns
Address valid to end of write	t_{AW}	20	—	30	—	40	—	ns
Address setup time	t_{AS}	0	—	0	—	0	—	ns
Write pulse width	t_{WP}	20	—	25	—	25	—	ns
Write recovery time	t_{WR}	3	—	3	—	3	—	ns
Data valid to end of write	t_{DW}	15	—	20	—	20	—	ns
Data hold time	t_{DH}	0	—	0	—	0	—	ns
Write enabled to output in high-Z	t_{WZ}^{*1}	0	15	0	20	0	25	ns
Output active from end of write	t_{OW}^{*1}	0	—	0	—	0	—	ns

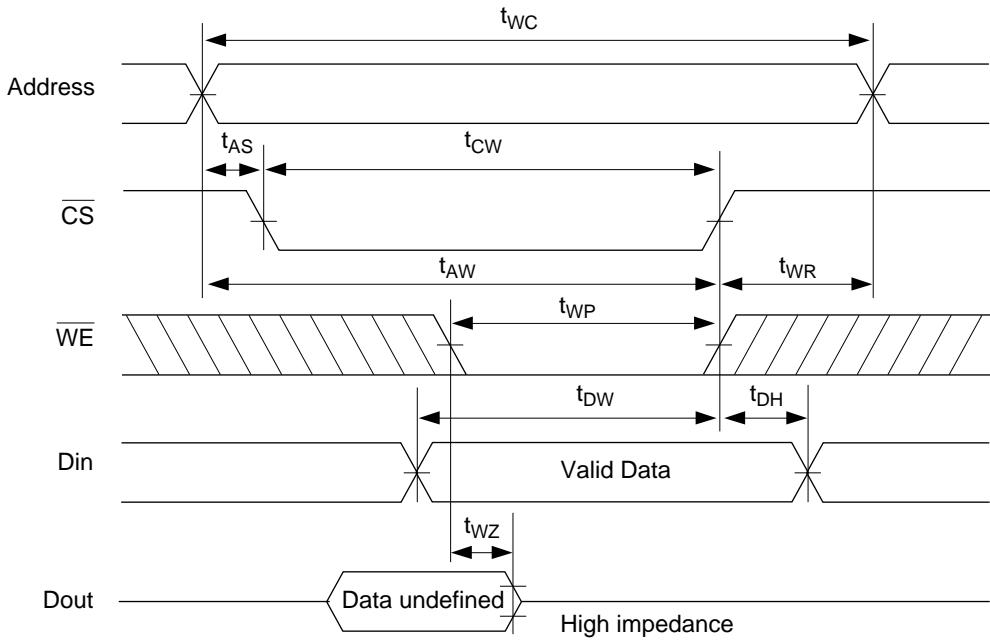
Note: 1. Transition is measured ± 200 mV from high-impedance voltage with Load (B).
 This parameter is sampled and is not 100% tested.

Write Timing Waveform (1) (\overline{WE} Controlled)



HM6207H Series

Write Timing Waveform (2) (\overline{CE} Controlled)



- Notes:
1. A write occurs during the overlap of a low \overline{CS} and a low \overline{WE} .
 2. t_{WR} is measured from the earlier of \overline{CS} or \overline{WE} going high to the end of the write cycle.
 3. If the \overline{CS} low transition occurs simultaneously with the \overline{WE} low transition, the output buffers remain in a high impedance state.
 4. Dout has the same phase as write data in this write cycle, if t_{WR} is long enough.

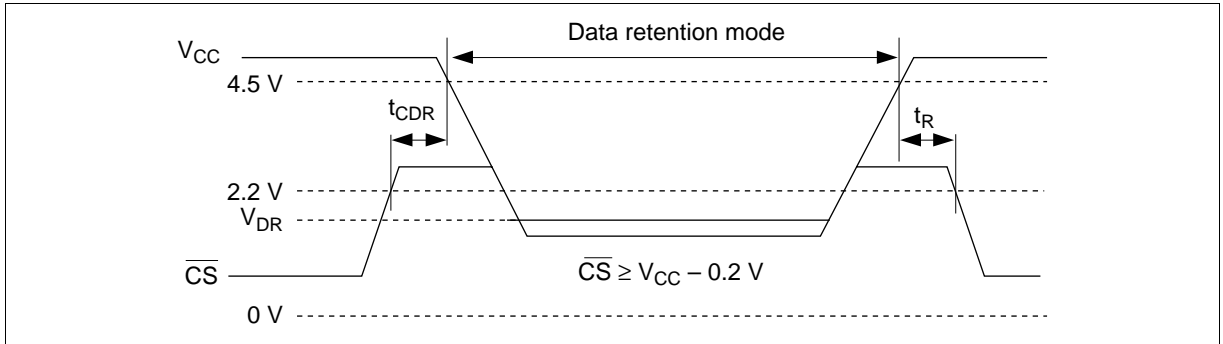
Low V_{CC} Data Retention Characteristics ($T_a = 0$ to $+70^\circ\text{C}$)

These characteristics are guaranteed for the L-version only.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$\overline{CS} \geq V_{CC} - 0.2$ V, $V_{in} \geq V_{CC} - 0.2$ V, or 0 V $\leq V_{in} \leq 0.2$ V
Data retention current	I_{CCDR}	—	2	50^{-1}	μA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	
Operation recovery time	t_R	5	—	—	ms	

Note: 1. $V_{CC} = 3.0$ V

Low V_{CC} Data Retention Timing Waveform

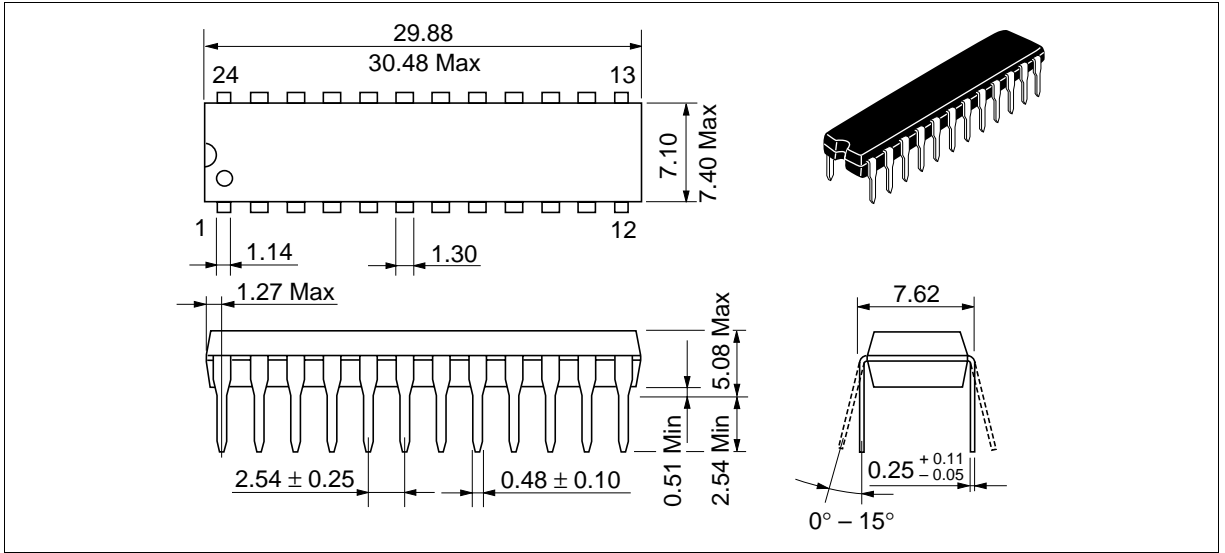


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Package Dimensions

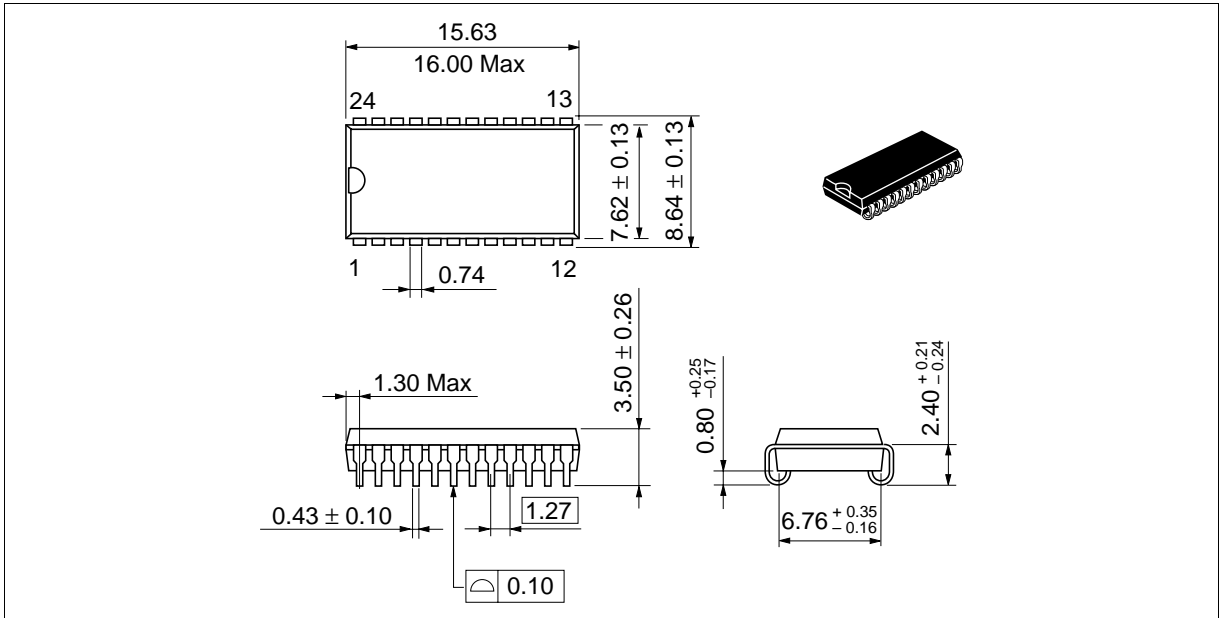
HM6207HP/HLP Series (DP-24NC)

Unit: mm



HM6207HJP/HLJP Series (CP-24D)

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brisbane, CA. 94005-1835

U S A

Tel: 415-589-8300

Fax: 415-583-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Dornacher Straße 3

D-85622 Feldkirchen

München

Tel: 089-9 91 80-0

Fax: 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 8YA

United Kingdom

Tel: 0628-585000

Fax: 0628-778322

Hitachi Asia Pte. Ltd.

16 Collyer Quay #20-00

Hitachi Tower

Singapore 0104

Tel: 535-2100

Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 706, North Tower,

World Finance Centre,

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel: 27359218

Fax: 27306071